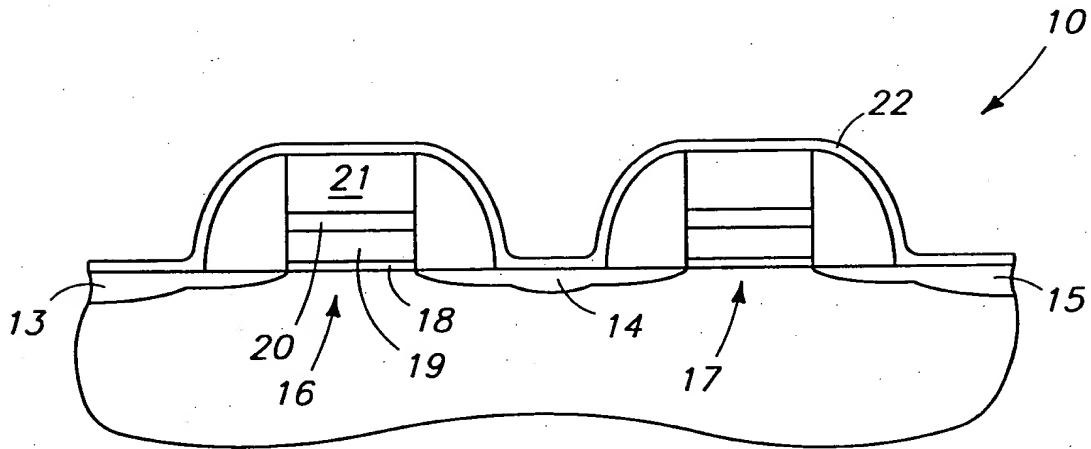
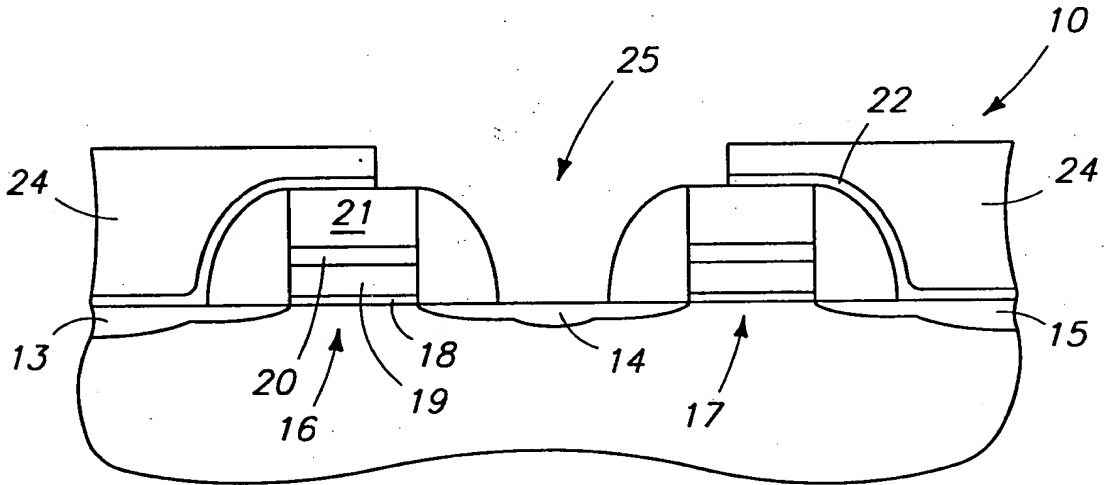


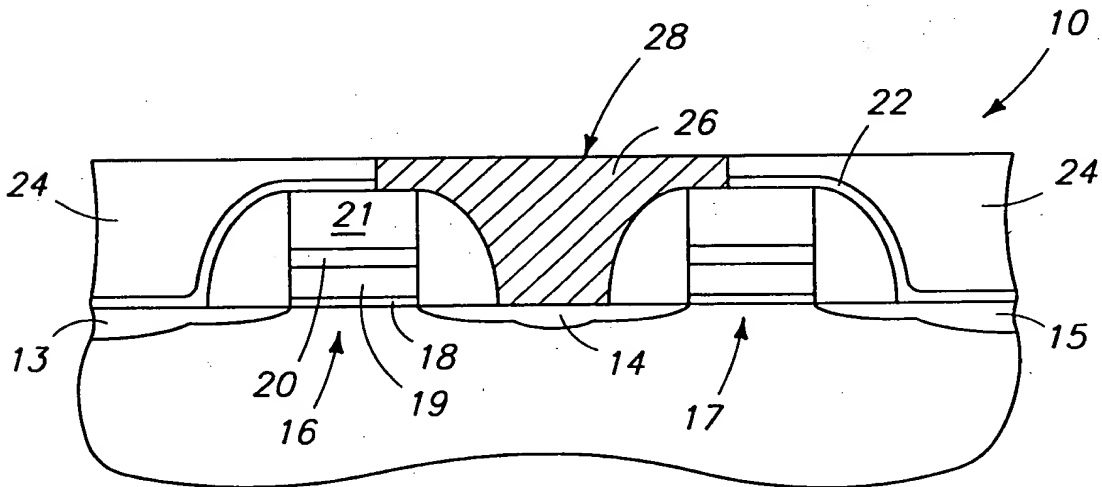
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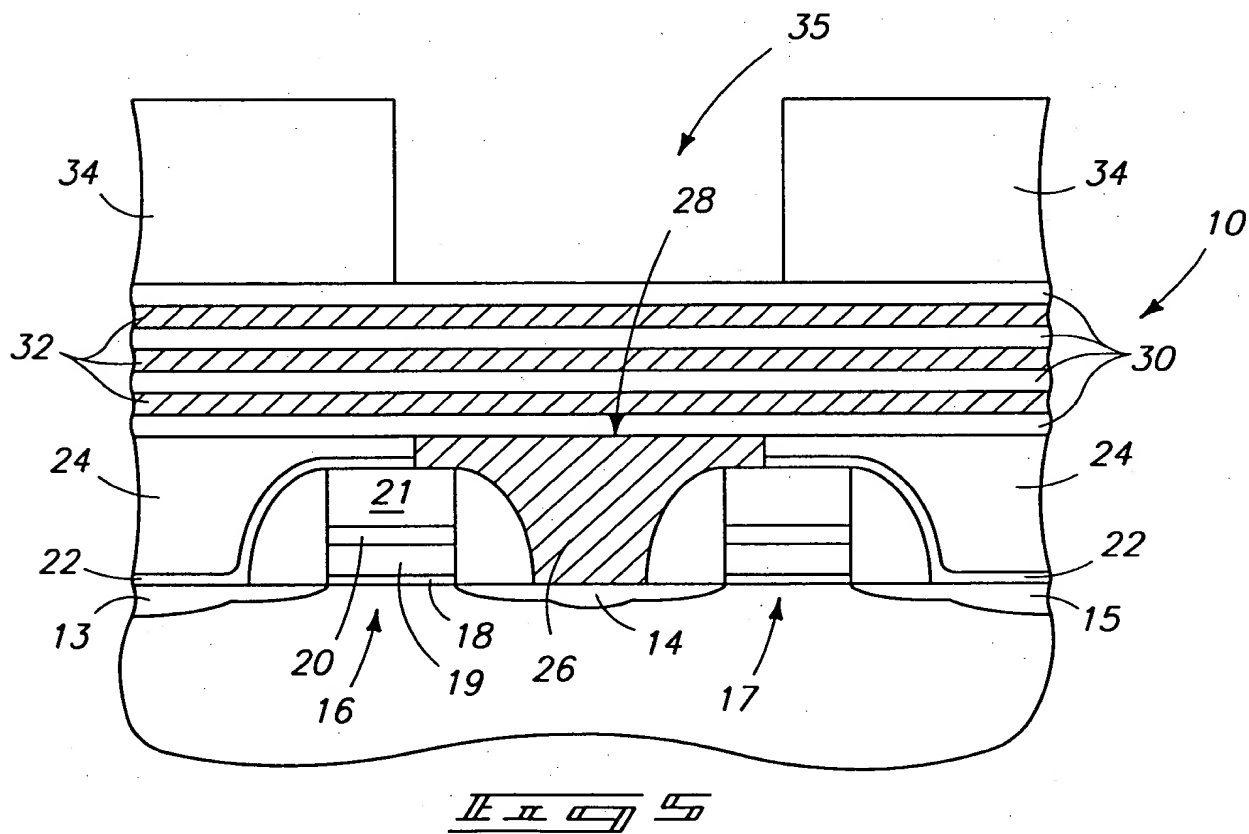
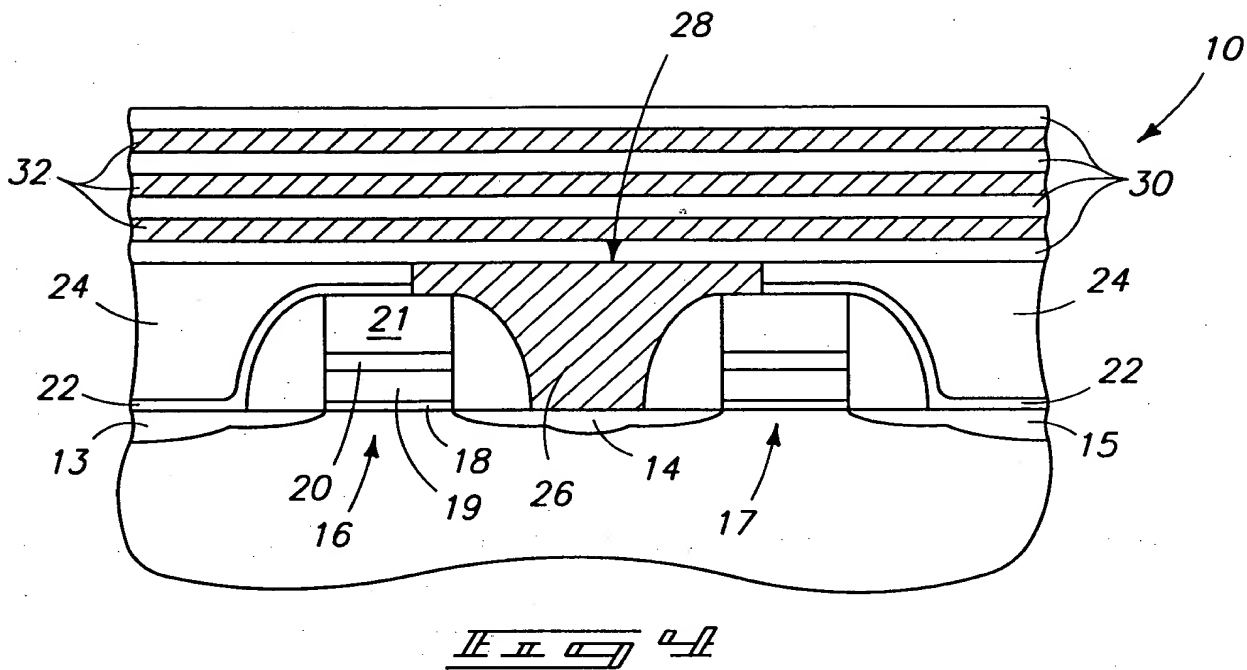
II



II

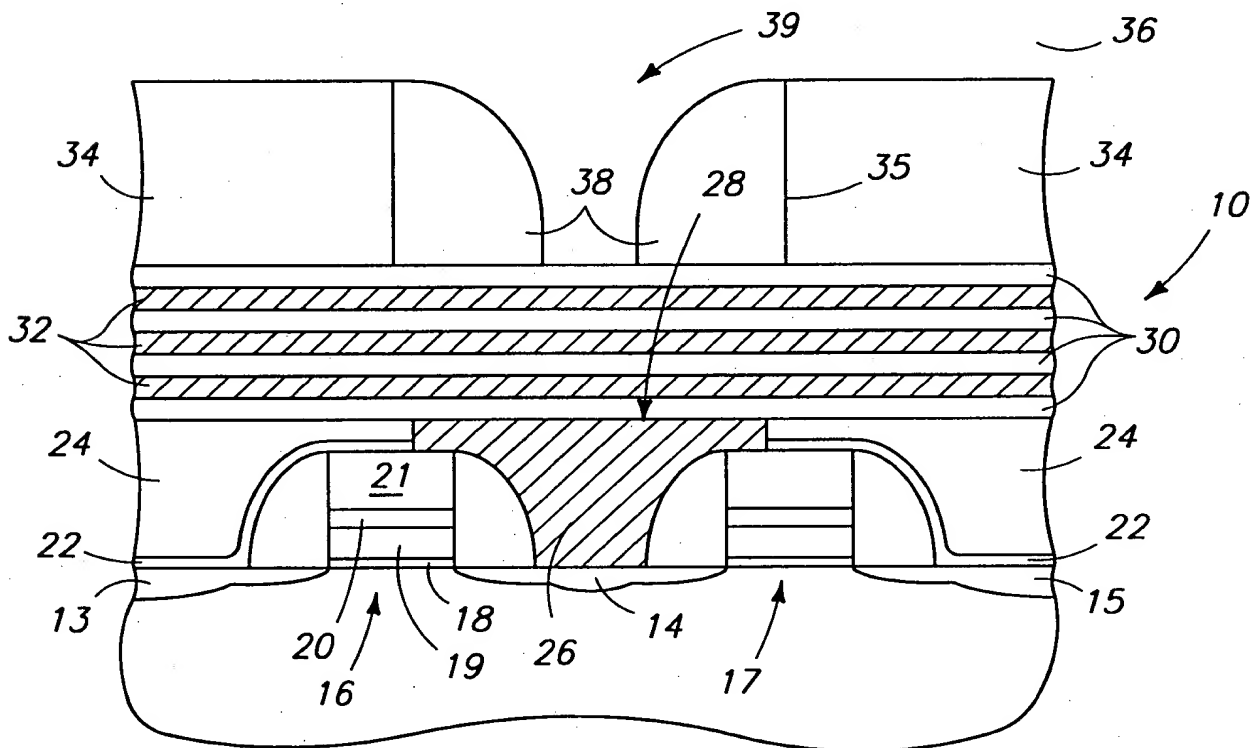
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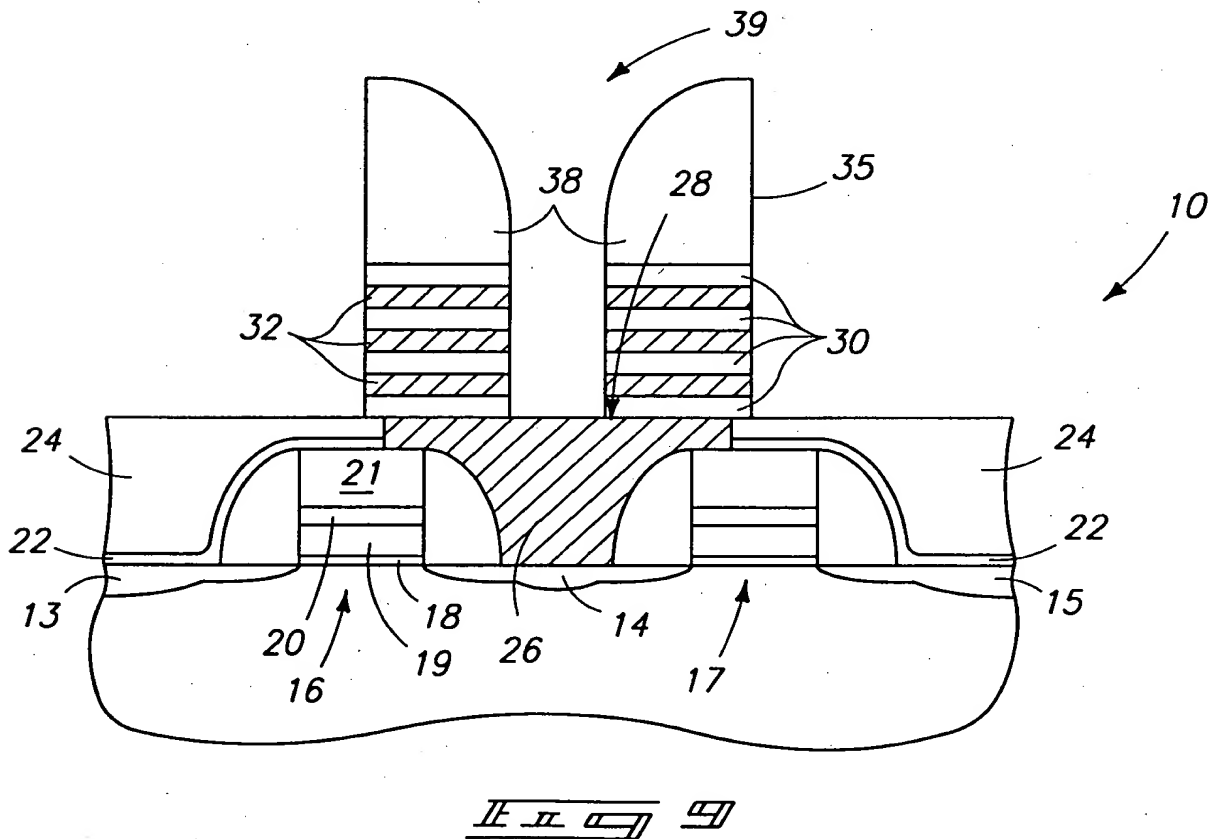
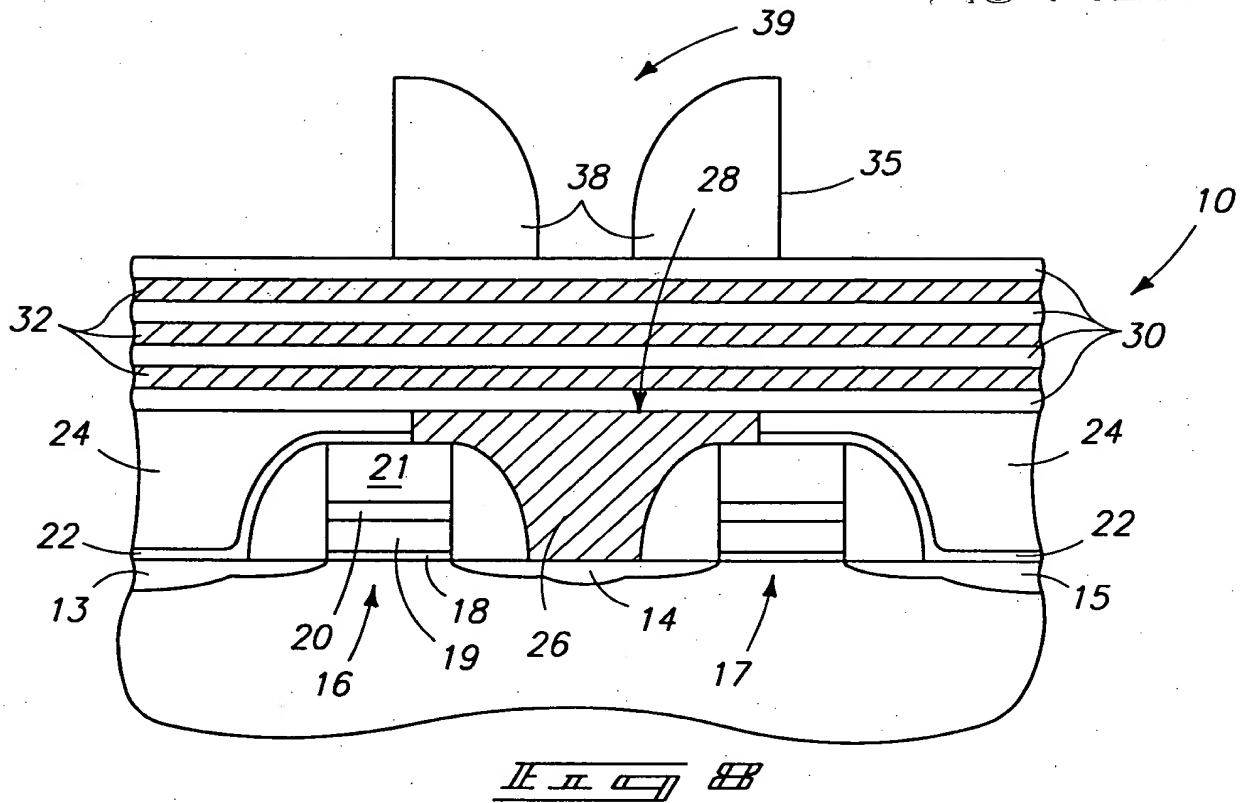
A cross-sectional view of a semiconductor device 10. The device features a substrate 13 with a base layer 15. A central region 14 is defined by a trench 16. Within this region, there is a structure 21, which includes a layer 20 and a layer 18. A layer 19 is located beneath the structure 21. A layer 22 is positioned above the base layer 15. A layer 24 is located above the layer 22. A layer 26 is positioned above the layer 24. A layer 28 is positioned above the layer 26. A layer 30 is positioned above the layer 28. A layer 32 is positioned above the layer 30. A layer 34 is positioned above the layer 32. A layer 35 is positioned above the layer 34. A layer 36 is positioned above the layer 35. The device is shown in a cross-sectional view, with various layers and structures labeled with numerical identifiers.

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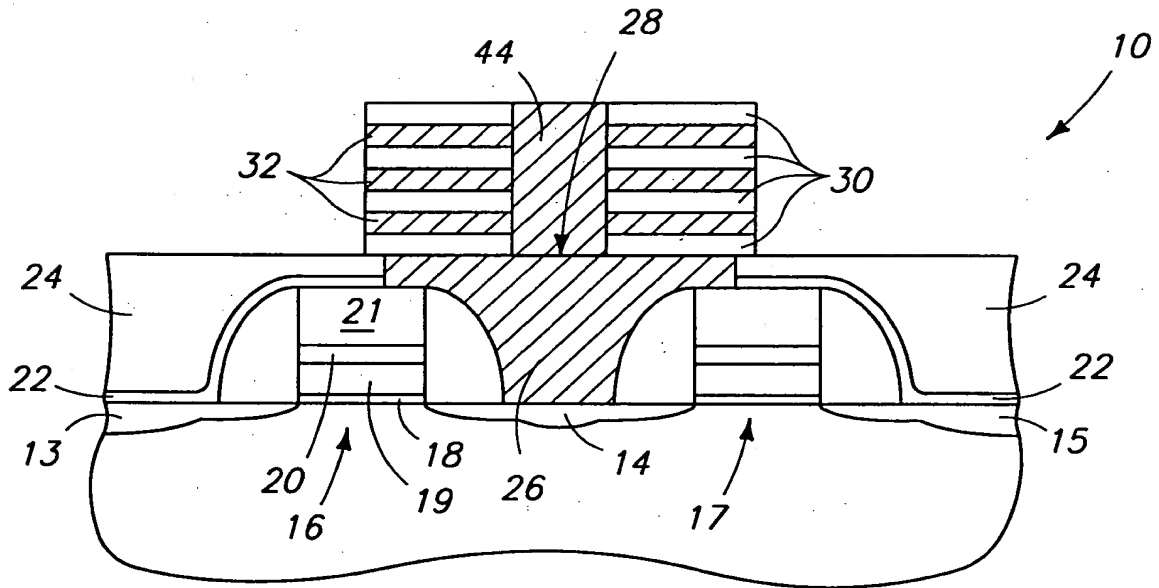


FIG. 1

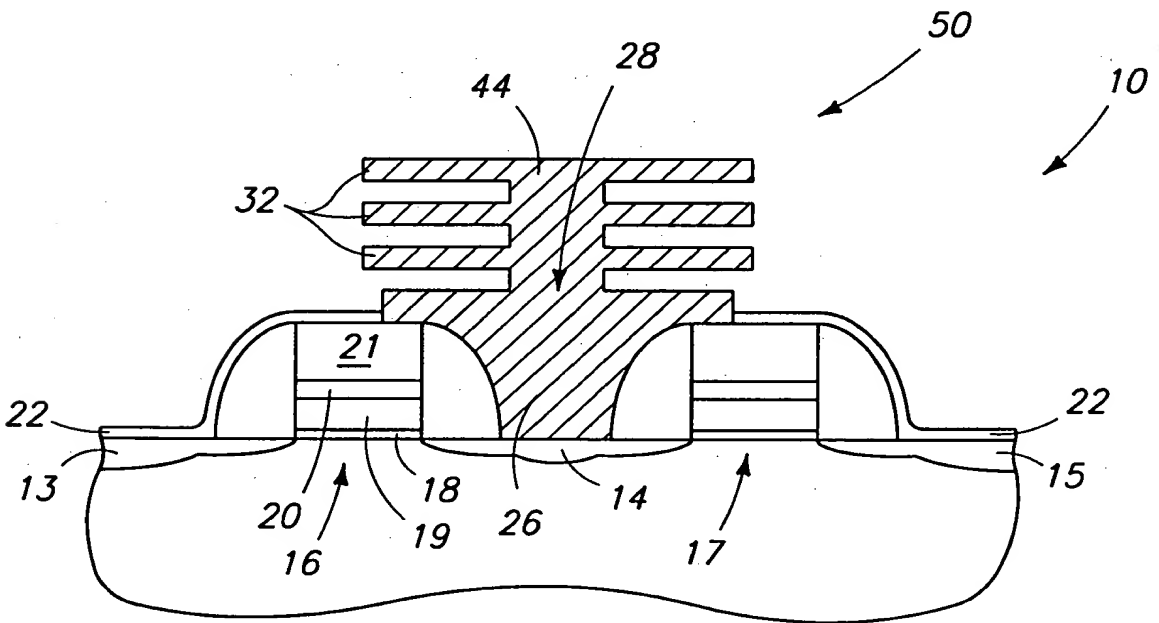


FIG. 2

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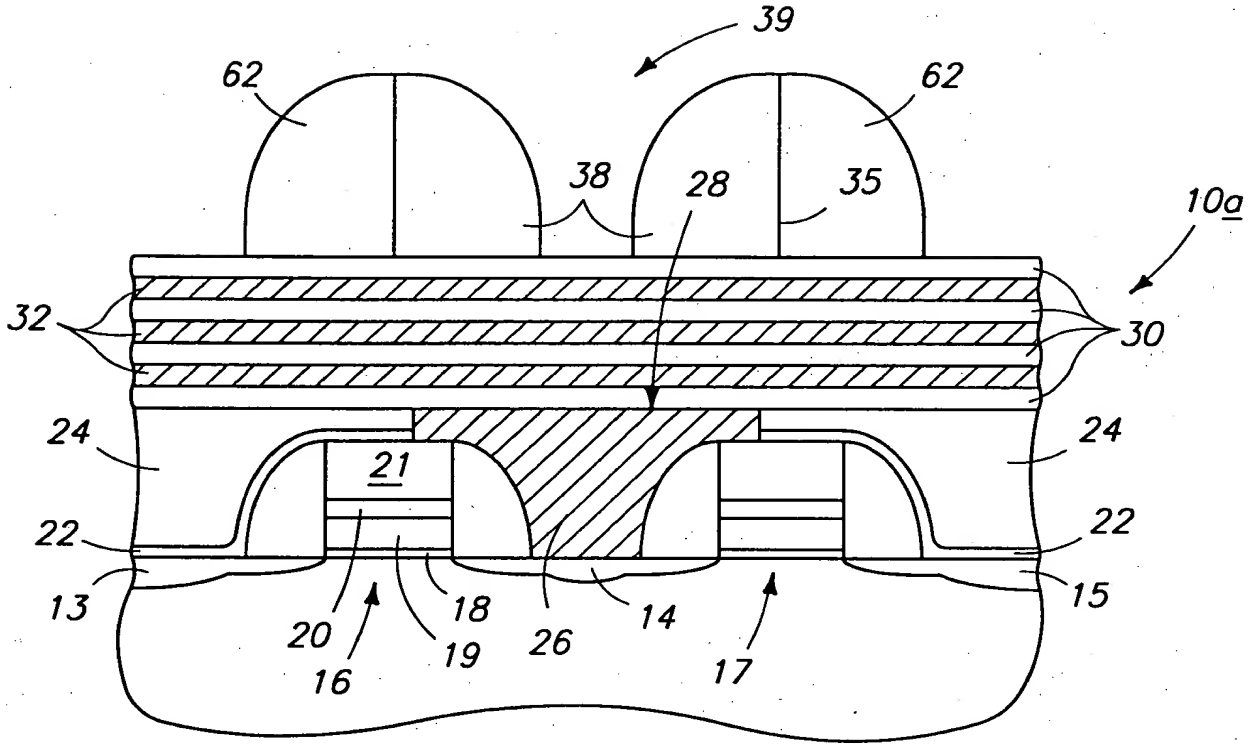


Fig. 1

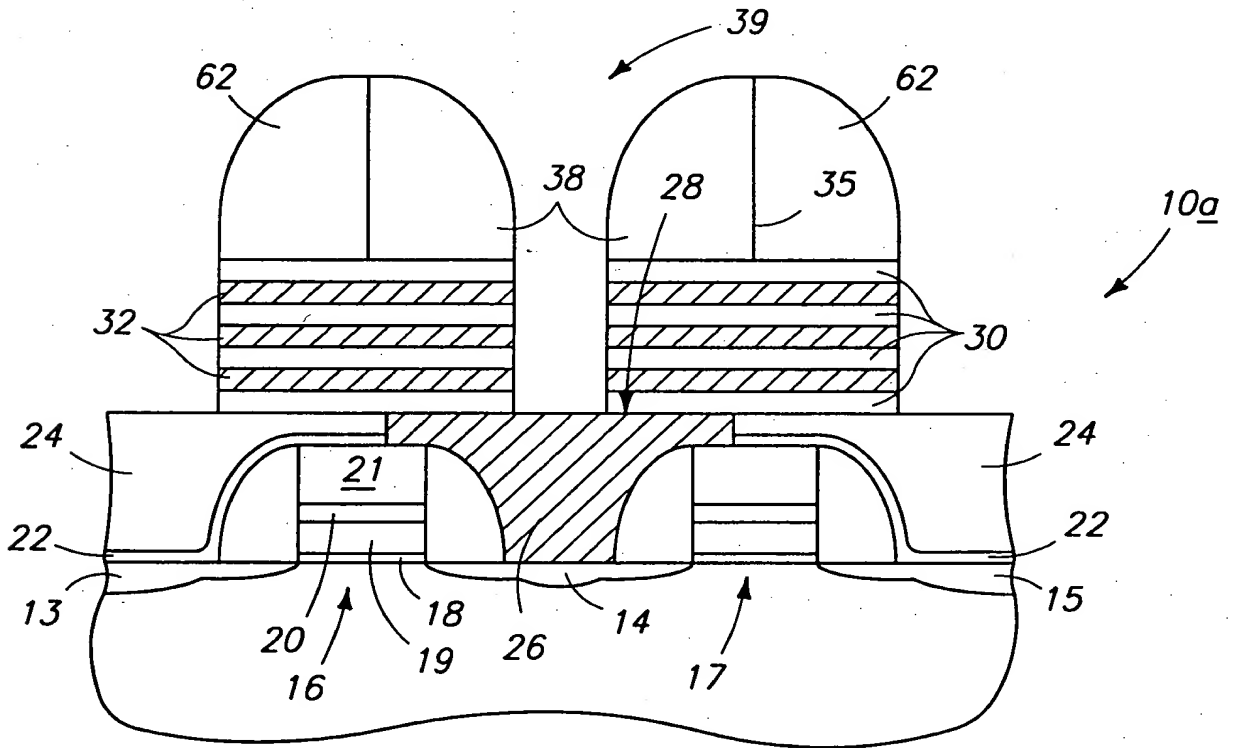


Fig. 2

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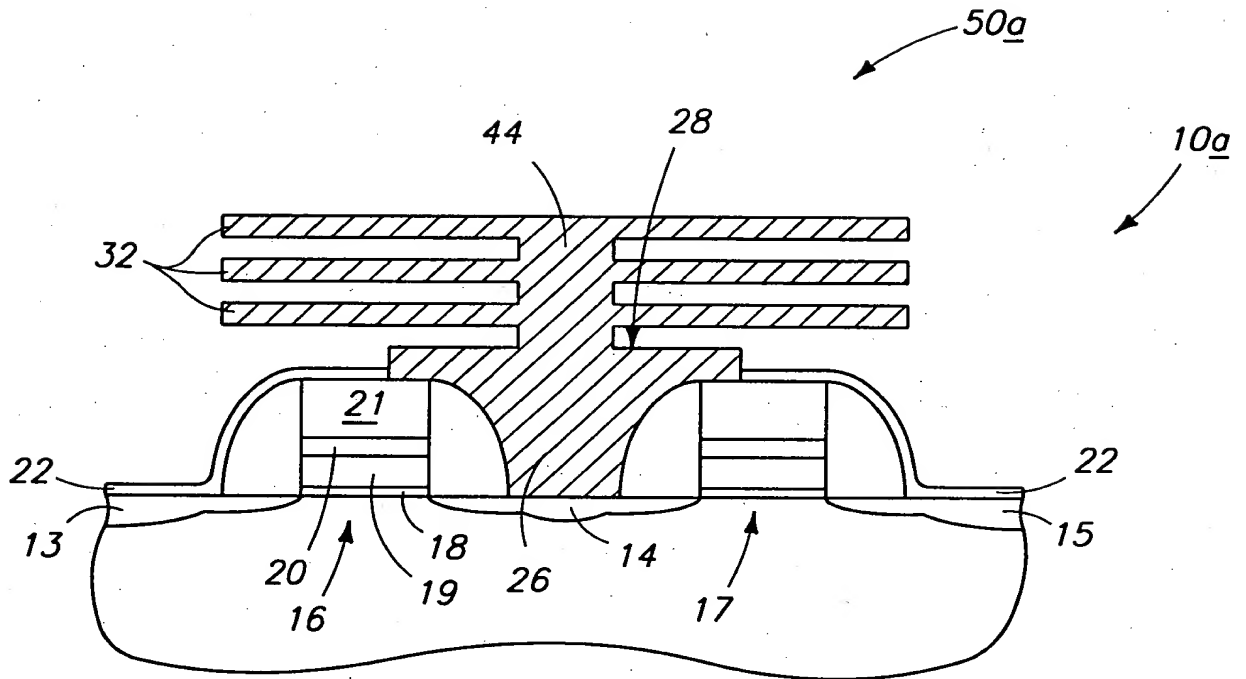
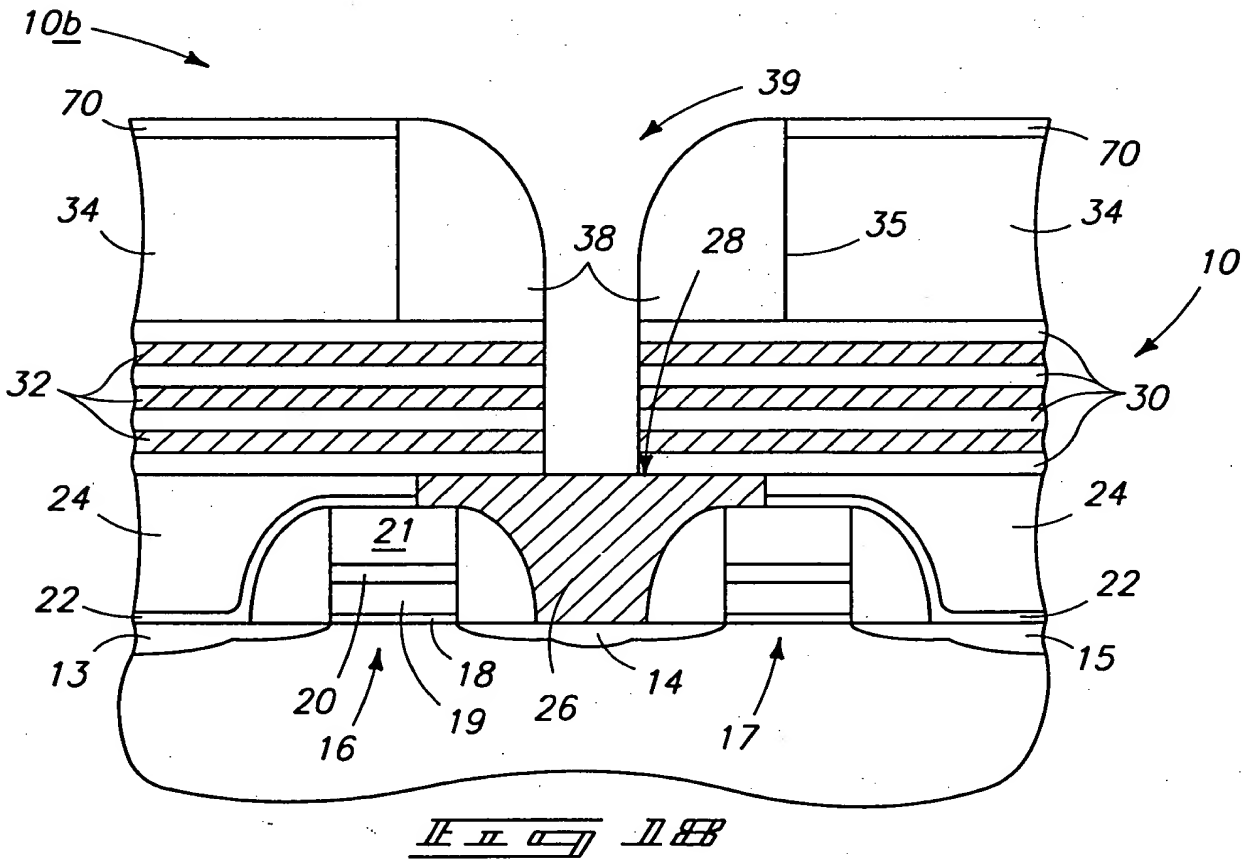
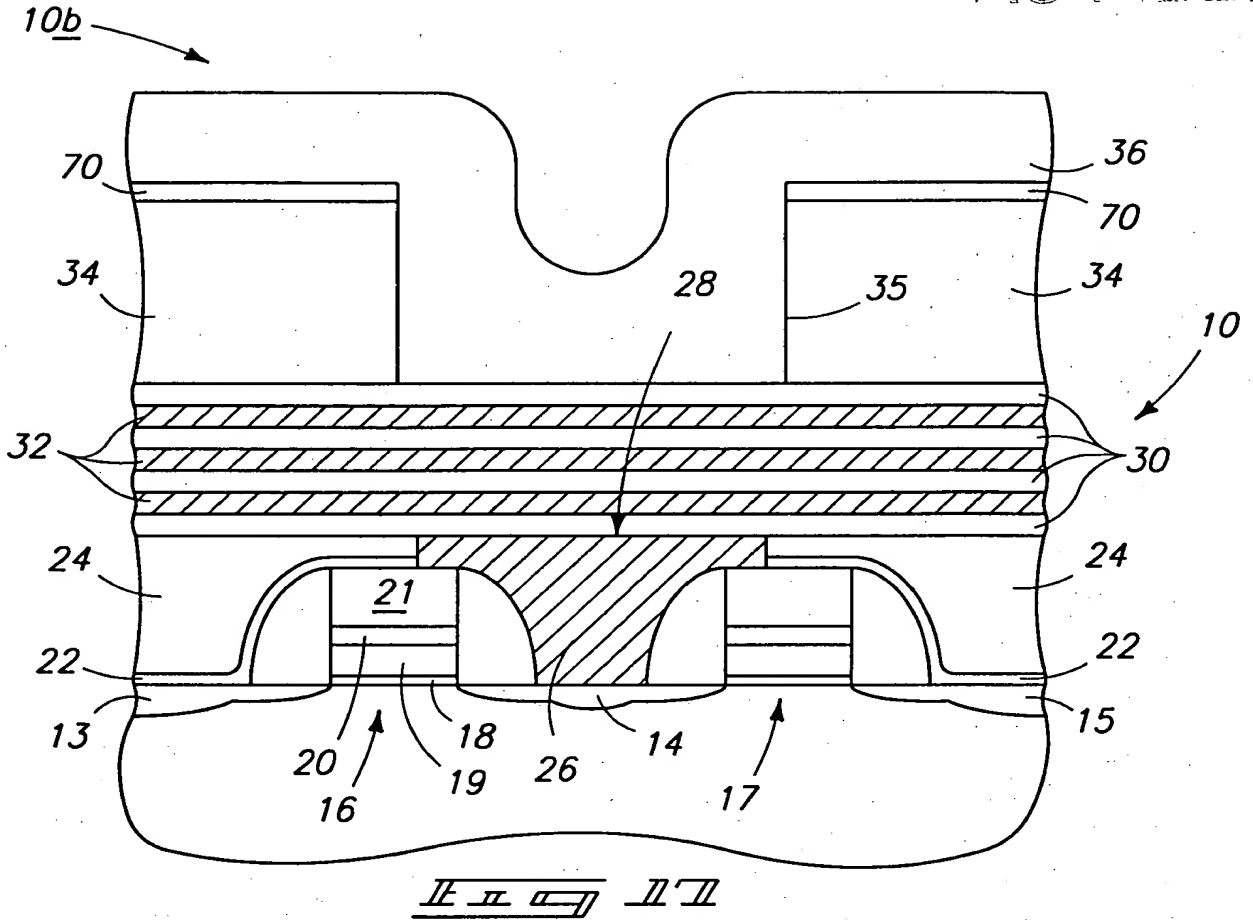


FIG. 11

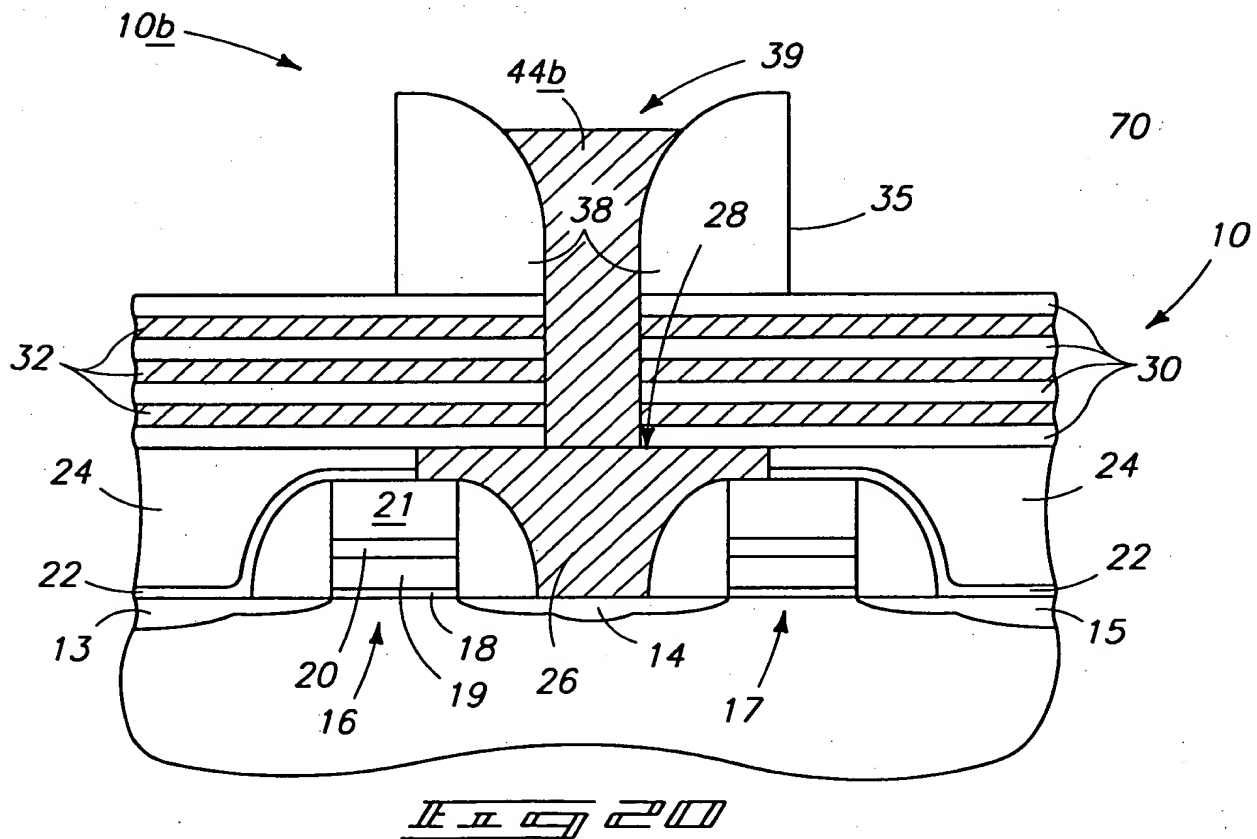
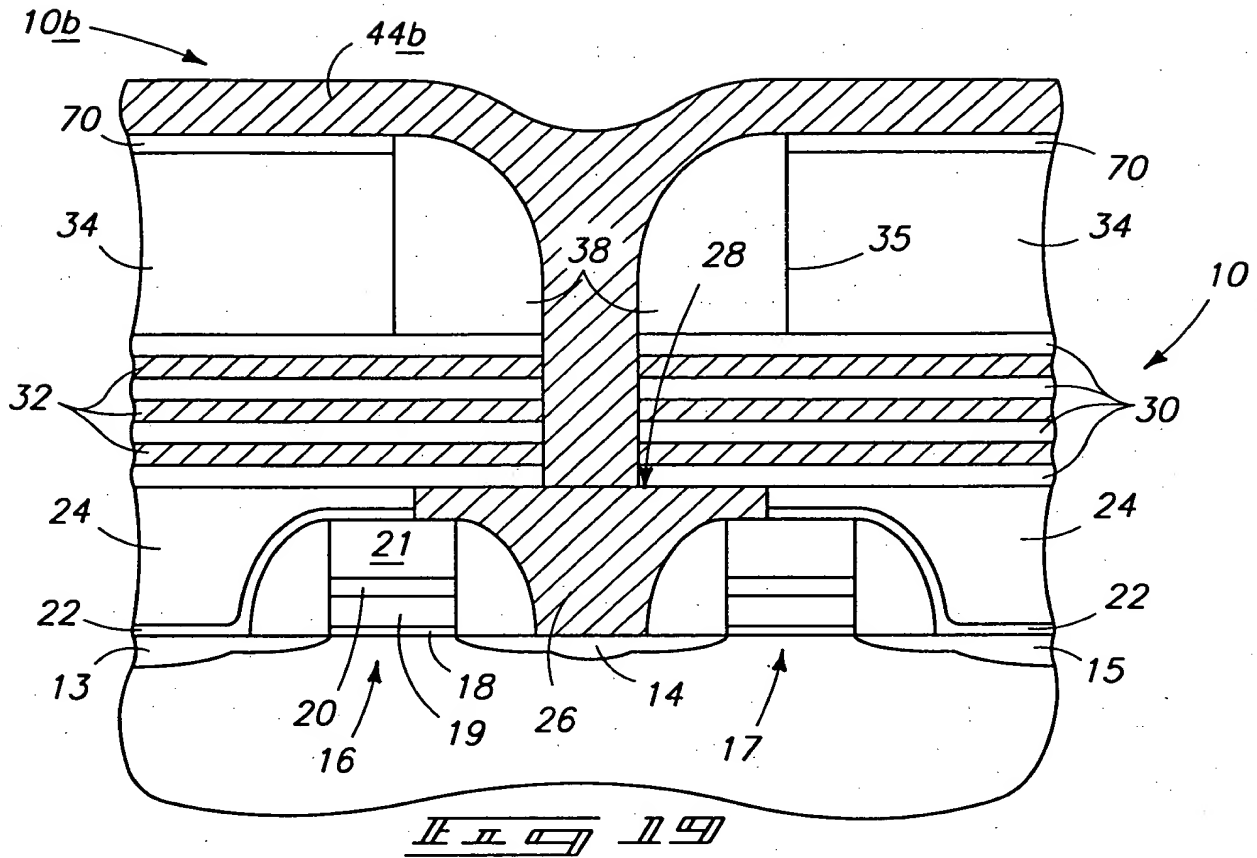
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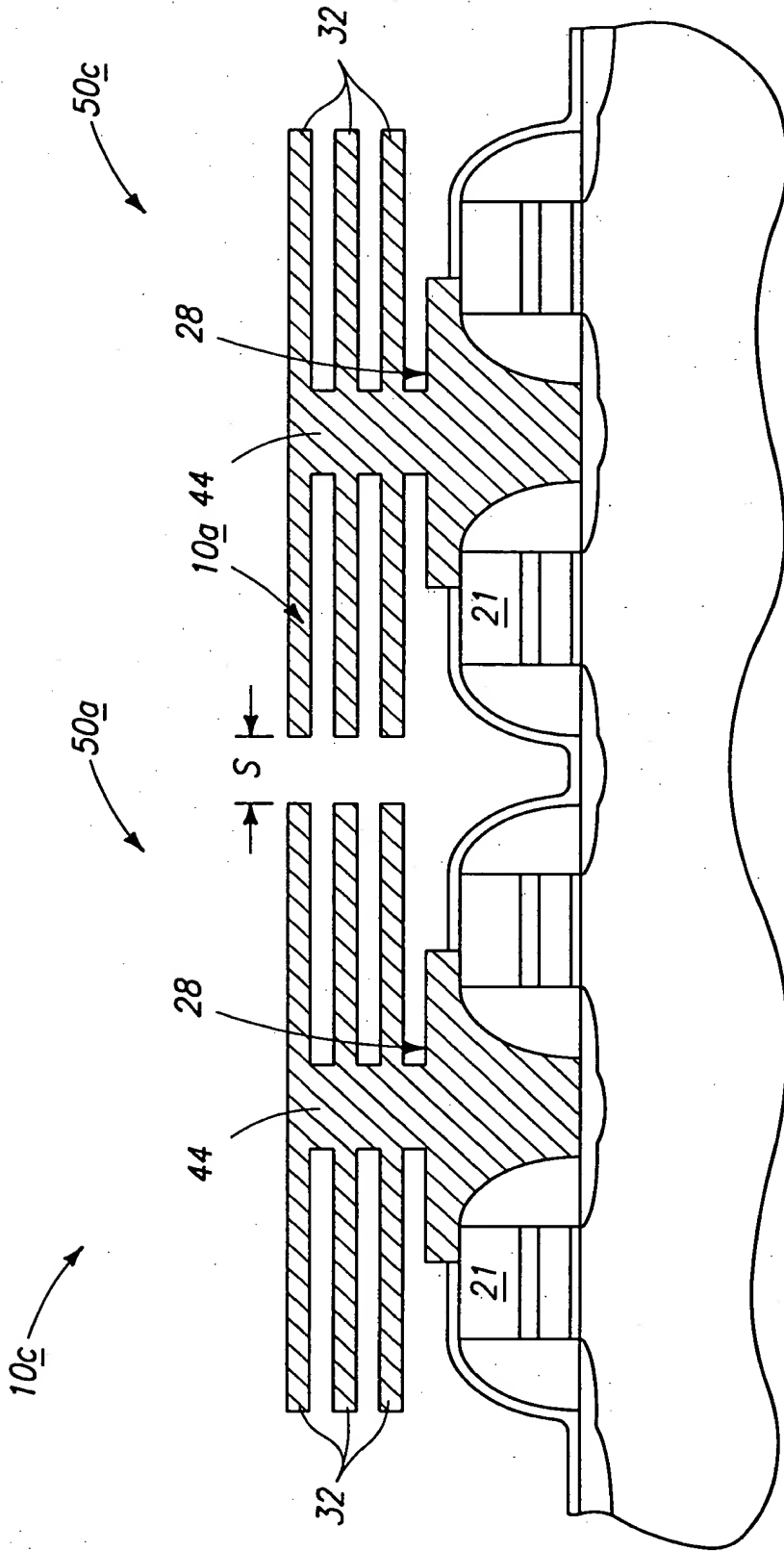


FIG. 22